Joaquim Puigdollers

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

137
papers

2,946
citations

h-index

49
g-index

149
ext. papers

2,946
dex
h-index

4.2
avg, IF

L-index

#	Paper	IF	Citations
137	Ultrathin Wide-Bandgap a-Si:H-Based Solar Cells for Transparent Photovoltaic Applications. <i>Solar Rrl</i> , 2022 , 6, 2100909	7.1	O
136	Atomic layer deposition of vanadium oxide films for crystalline silicon solar cells <i>Materials Advances</i> , 2022 , 3, 337-345	3.3	5
135	Interdigitated back-contacted crystalline silicon solar cells fully manufactured with atomic layer deposited selective contacts. <i>Solar Energy Materials and Solar Cells</i> , 2022 , 240, 111731	6.4	2
134	Effect of the thickness of amorphous silicon carbide interlayer on the passivation of c-Ge surface by aluminium oxide films. <i>Surfaces and Interfaces</i> , 2022 , 31, 102070	4.1	1
133	Synergetic effect induced/tuned bimetallic nanoparticles (Pt-Ni) anchored graphene as a catalyst for oxygen reduction reaction and scalable SS-314L serpentine flow field proton exchange membrane fuel cells (PEMFCs). Materials Science and Engineering B: Solid-State Materials for	3.1	O
132	Towards the Bisbenzothienocarbazole Core: A Route of Sulfurated Carbazole Derivatives with Assorted Optoelectronic Properties and Applications. <i>Materials</i> , 2021 , 14,	3.5	1
131	Hole Transport Layer based on atomic layer deposited V2Ox films: Paving the road to semi-transparent CZTSe solar cells. <i>Solar Energy</i> , 2021 , 226, 64-71	6.8	O
130	Shedding Light on the Negative Differential Resistance Effect Observed in Organic Thin-Film Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 1574-1582	4	1
129	Transition-Metal Oxides for Kesterite Solar Cells Developed on Transparent Substrates. <i>ACS Applied Materials & Developed on Transparent Substrates</i> . <i>ACS Applied Materials & Developed on Transparent Substrates</i> . <i>ACS Applied Materials & Developed on Transparent Substrates</i> . <i>ACS Applied Materials & Developed on Transparent Substrates</i> .	9.5	21
128	Origin of the Negative Differential Resistance in the Output Characteristics of a Picene-Based Thin-Film Transistor. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 391-395	2.3	
127	Low-Cost High-Sensitive Suns[\$V_{text{oc}}\$ Measurement Instrument to Characterize c-Si Solar Cells. <i>IEEE Transactions on Instrumentation and Measurement</i> , 2020 , 69, 6429-6435	5.2	4
126	Enhanced Chiral Sensing with Dielectric Nanoresonators. <i>Nano Letters</i> , 2020 , 20, 585-591	11.5	51
125	Influence of Co-Sputtered Ag:Al Ultra-Thin Layers in Transparent VO/Ag:Al/AZO Hole-Selective Electrodes for Silicon Solar Cells. <i>Materials</i> , 2020 , 13,	3.5	4
124	Near 5% DMSO is the best: A structural investigation of PEDOT: PSS thin films with strong emphasis on surface and interface for hybrid solar cell. <i>Applied Surface Science</i> , 2020 , 499, 143967	6.7	26
123	Satisfying both interfacial- and bulk requirements for organic photovoltaics: Bridged-triphenylamines with extended Etonjugated systems as efficient new molecules. <i>Organic Electronics</i> , 2019 , 73, 137-145	3.5	3
122	Improved Electron Selectivity in Silicon Solar Cells by Cathode Modification with a Dipolar Conjugated Polyelectrolyte Interlayer. <i>ACS Applied Energy Materials</i> , 2019 , 2, 5954-5959	6.1	4
121	Multicrystalline Silicon Thin-Film Solar Cells Based on Vanadium Oxide Heterojunction and Laser-Doped Contacts. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1900393	1.6	4

120	Influence of a Gold Seed in Transparent V2Ox/Ag/V2Ox Selective Contacts for Dopant-Free Silicon Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2019 , 9, 72-77	3.7	5
119	Defect states assisted charge conduction in Au/MoO3☑/n-Si Schottky barrier diode. <i>Materials Research Express</i> , 2019 , 6, 036303	1.7	10
118	Reduction of Charge Traps and Stability Enhancement in Solution-Processed Organic Field-Effect Transistors Based on a Blended n-Type Semiconductor. <i>ACS Applied Materials & Discrete Amp; Interfaces</i> , 2018 , 10, 15952-15961	9.5	36
117	Interdigitated back-contacted crystalline silicon solar cells with low-temperature dopant-free selective contacts. <i>Journal of Materials Chemistry A</i> , 2018 , 6, 3977-3985	13	36
116	Temperature dependent current-voltage characteristics of Au/n-Si Schottky barrier diodes and the effect of transition metal oxides as an interface layer. <i>Physica B: Condensed Matter</i> , 2018 , 530, 327-335	2.8	39
115	Transport mechanisms in silicon heterojunction solar cells with molybdenum oxide as a hole transport layer. <i>Solar Energy Materials and Solar Cells</i> , 2018 , 185, 61-65	6.4	29
114	Static and dynamic modeling of organic thin film transistors: effect of channel length on the Mayer Neldel rule energy and quasistatic capacitances. <i>EPJ Applied Physics</i> , 2018 , 81, 30202	1.1	1
113	Air stable organic semiconductors based on diindolo[3,2-a:3?,2?-c]carbazole. <i>Organic Electronics</i> , 2018 , 62, 35-42	3.5	5
112	Interface engineering and solid-state organization for triindole-based p-type organic thin-film transistors. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 17889-17898	3.6	12
111	Solid-state organization of n-type carbazole-based semiconductors for organic thin-film transistors. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 1142-1149	3.6	15
110	Enantiomer-Selective Molecular Sensing Using Racemic Nanoplasmonic Arrays. <i>Nano Letters</i> , 2018 , 18, 6279-6285	11.5	83
109	Rapid room temperature crystallization of TiO2 nanotubes. <i>CrystEngComm</i> , 2017 , 19, 1585-1589	3.3	12
108	V2Ox-based hole-selective contacts for c-Si interdigitated back-contacted solar cells. <i>Journal of Materials Chemistry A</i> , 2017 , 5, 9182-9189	13	78
107	Superior performance of V 2 O 5 as hole selective contact over other transition metal oxides in silicon heterojunction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 168, 221-226	6.4	90
106	Interdigitated back contacted c-Si(p) solar cells with photovoltaic efficiencies beyond 22% 2017 ,		2
105	Origin of passivation in hole-selective transition metal oxides for crystalline silicon heterojunction solar cells. <i>Journal of Materials Research</i> , 2017 , 32, 260-268	2.5	102
104	Passivating/hole-selective contacts based on V2O5/SiOx stacks deposited at ambient temperature. <i>Energy Procedia</i> , 2017 , 124, 584-592	2.3	24
103	Analysis of temperature dependent current-voltage and capacitance-voltage characteristics of an Au/V2O5/n-Si Schottky diode. <i>AIP Advances</i> , 2017 , 7, 085313	1.5	43

102	High efficiency ITO-free hybrid solar cell using highly conductive PEDOT:PSS with co-solvent and surfactant treatments. <i>Materials Letters</i> , 2017 , 186, 165-167	3.3	11
101	Transition metal oxides as hole-selective contacts in silicon heterojunctions solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 145, 109-115	6.4	254
100	Fabrication of cost-effective, highly reproducible large area arrays of nanotriangular pillars for surface enhanced Raman scattering substrates. <i>Nano Research</i> , 2016 , 9, 3075-3083	10	21
99	PEDOT:PSS as an Alternative Hole Selective Contact for ITO-Free Hybrid Crystalline Silicon Solar Cell. <i>IEEE Journal of Photovoltaics</i> , 2016 , 6, 934-939	3.7	20
98	Characterization and modeling of organic thin-film transistors based Econjugated small molecule tetraphenyldibenzoperiflanthene: Effects of channel length. <i>Microelectronic Engineering</i> , 2016 , 160, 39-	48 ⁵	18
97	Temperature dependence of the electrical properties of organic thin-film transistors based on tetraphenyldibenzoperiflanthene deposited at different substrate temperatures: Experiment and modeling. <i>Microelectronic Engineering</i> , 2016 , 150, 47-56	2.5	18
96	A Rapid, Low-Cost, and Scalable Technique for Printing State-of-the-Art Organic Field-Effect Transistors. <i>Advanced Materials Technologies</i> , 2016 , 1, 1600090	6.8	65
95	Intermittent chaos for ergodic light trapping in a photonic fiber plate. <i>Light: Science and Applications</i> , 2016 , 5, e16216	16.7	15
94	Back Junction n-type Silicon Heterojunction Solar Cells with V2O5 Hole-selective Contact. <i>Energy Procedia</i> , 2016 , 92, 633-637	2.3	21
93	Experimental determination of base resistance contribution for point-like contacted c-Si solar cells using impedance spectroscopy analysis. <i>Solar Energy Materials and Solar Cells</i> , 2015 , 141, 350-355	6.4	2
92	Experimental study and analytical modeling of the channel length influence on the electrical characteristics of small-molecule thin-film transistors. <i>Superlattices and Microstructures</i> , 2015 , 83, 224-2	36 8	23
91	Large Stokes shift downshifting Eu(III) films as efficiency enhancing UV blocking layers for dye sensitized solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 203-210	1.6	20
90	Reversibility of humidity effects in pentacene based organic thin-film transistor: Experimental data and electrical modeling. <i>Synthetic Metals</i> , 2015 , 199, 303-309	3.6	29
89	Molecular order of air-stable p-type organic thin-film transistors by tuning the extension of the Etonjugated core: the cases of indolo[3,2-b]carbazole and triindole semiconductors. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 506-513	7.1	65
88	Characterization of Transition Metal Oxide/Silicon Heterojunctions for Solar Cell Applications. <i>Applied Sciences (Switzerland)</i> , 2015 , 5, 695-705	2.6	66
87	High efficiency interdigitated back-contact c-Si(p) solar cells 2015 ,		2
86	Compositional influence on the electrical performance of zinc indium tin oxide transparent thin-film transistors. <i>Thin Solid Films</i> , 2014 , 555, 107-111	2.2	3
85	A compact tetrathiafulvalene-benzothiadiazole dyad and its highly symmetrical charge-transfer salt: ordered donor Estacks closely bound to their acceptors. <i>Chemistry - A European Journal</i> , 2014 , 20, 7136-43	4.8	23

(2010-2014)

84	Restraints in low dimensional organic semiconductor devices at high current densities. <i>Organic Electronics</i> , 2014 , 15, 211-215	3.5	1	
83	Influence of the density of states on the open-circuit voltage in small-molecule solar cells. <i>Organic Electronics</i> , 2014 , 15, 2553-2560	3.5	11	
82	HOMO stabilisation in Extended dibenzotetrathiafulvalene derivatives for their application in organic field-effect transistors. <i>Chemistry - A European Journal</i> , 2014 , 20, 16672-9	4.8	13	
81	Vertically aligned ZnO nanorod array/CuO heterojunction for UV detector application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2493-2498	1.6	15	
80	Degradation study and calculation of density-of-states in PTCDI-C8 channel layer from the electrical characteristics of thin-film transistors. <i>Journal of Applied Physics</i> , 2014 , 116, 024507	2.5	9	
79	Progress in silicon heterojunction solar cell fabrication with rear laser-fired contacts 2013,		2	
78	Analysis of the dynamic short-circuit resistance in organic bulk-heterojunction solar cells: relation to the charge carrier collection efficiency. <i>Organic Electronics</i> , 2013 , 14, 1643-1648	3.5	10	
77	Simulation of organic inverter. <i>Solid-State Electronics</i> , 2012 , 68, 18-21	1.7	5	
76	Organic metal B rganic semiconductor blended contacts in single crystal field-effect transistors. Journal of Materials Chemistry, 2012 , 22, 16011		13	
75	Comparison between the density-of-states of picene transistors measured in air and under vacuum. <i>Synthetic Metals</i> , 2012 , 161, 2554-2557	3.6	9	
74	Evidence of intrinsic ambipolar charge transport in a high band gap organic semiconductor. <i>Journal of Materials Chemistry</i> , 2012 , 22, 345-348		8	
73	Determination of the Density of States on N-type Ptcdi-c13 Organic Thin-film Semiconductor. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1435, 36			
72	Electronic and structural characterisation of a tetrathiafulvalene compound as a potential candidate for ambipolar transport properties. <i>CrystEngComm</i> , 2011 , 13, 6597	3.3	16	
71	Electron-Withdrawing Substituted Tetrathiafulvalenes as Ambipolar Semiconductors II Chemistry of Materials, 2011 , 23, 851-861	9.6	29	
70	2011,		6	
69	CURRENT AND VOLTAGE SIMULATION OF AN ORGANIC INVERTER. International Journal of High Speed Electronics and Systems, 2011 , 20, 843-851	0.5	1	
68	Interchain and intrachain emission branching in polymer light-emitting diode doped by organic molecules. <i>Applied Physics Letters</i> , 2010 , 96, 033301	3.4	9	
67	Density-of-states in pentacene from the electrical characteristics of thin-film transistors. <i>Organic Electronics</i> , 2010 , 11, 1333-1337	3.5	37	

66	Optical stability of small-molecule thin-films determined by Photothermal Deflection Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1154, 1		3
65	A comparative study of hydrogen- and hydroxyl-related pentacene defect formation in thin films prepared by Langmuir B lodgett technique and thermal evaporation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1404-1409	1.6	4
64	N-type PTCDI I 13H27 thin-film transistors deposited at different substrate temperature. <i>Thin Solid Films</i> , 2009 , 517, 6271-6274	2.2	27
63	Optoelectronic properties of CuPc thin films deposited at different substrate temperatures. Journal Physics D: Applied Physics, 2009 , 42, 145102	3	40
62	2009,		2
61	Defect states in pentacene thin films prepared by thermal evaporation and Langmuir B lodgett technique. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 2888-2891	3.9	7
60	Optical and Morphological Characterization of PTCDI-C13. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1091, 1		O
59	Recombination rates in heterojunction silicon solar cells analyzed by impedance spectroscopy at forward bias and under illumination. <i>Solar Energy Materials and Solar Cells</i> , 2008 , 92, 505-509	6.4	55
58	Progress in a-Si:H/c-Si heterojunction emitters obtained by Hot-Wire CVD at 200 LC. <i>Thin Solid Films</i> , 2008 , 516, 761-764	2.2	12
57	Very low surface recombination velocity of crystalline silicon passivated by phosphorus-doped a-SicxNy:H(n) alloys. <i>Progress in Photovoltaics: Research and Applications</i> , 2008 , 16, 123-127	6.8	13
56	Fullerene thin-film transistors fabricated on polymeric gate dielectric. <i>Thin Solid Films</i> , 2007 , 515, 7667	-7 <u>6</u> .70	8
55	Improving the efficiency of light-emitting diode based on a thiophene polymer containing a cyano group. <i>Organic Electronics</i> , 2007 , 8, 641-647	3.5	10
54	Photodiodes based on fullerene semiconductor. <i>Thin Solid Films</i> , 2007 , 515, 7675-7678	2.2	14
53	Optical study of polymer infiltration into porous Si based structures 2007 ,		3
52	Experimental observation of oxygen-related defect state in pentacene thin films. <i>Applied Physics Letters</i> , 2007 , 90, 092112	3.4	36
51	Bifacial heterojunction silicon solar cells by hot-wire CVD with open-circuit voltages exceeding 600 mV. <i>Thin Solid Films</i> , 2006 , 511-512, 415-419	2.2	20
50	Effect of buffer layer on minority carrier lifetime and series resistance of bifacial heterojunction silicon solar cells analyzed by impedance spectroscopy. <i>Thin Solid Films</i> , 2006 , 514, 254-257	2.2	26
49	Characterization of bifacial heterojunction silicon solar cells obtained by hot-wire CVD. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1953-1957	3.9	4

(2002-2006)

48	Low level optical absorption measurements on organic semiconductors. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1663-1667	3.9	17
47	Copper phthalocyanine thin-film transistors with polymeric gate dielectric. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 1778-1782	3.9	51
46	Study of a thiophene-based polymer for optoelectronic applications. <i>Thin Solid Films</i> , 2006 , 497, 16-19	2.2	25
45	Electronic properties of intrinsic and doped amorphous silicon carbide films. <i>Thin Solid Films</i> , 2006 , 511-512, 290-294	2.2	13
44	Optoelectronic devices based on evaporated pentacene films. <i>Solar Energy Materials and Solar Cells</i> , 2005 , 87, 567-573	6.4	31
43	Phosphorus-diffused silicon solar cell emitters with plasma enhanced chemical vapor deposited silicon carbide. <i>Solar Energy Materials and Solar Cells</i> , 2005 , 87, 667-674	6.4	10
42	Accurate modeling and parameter extraction method for organic TFTs. <i>Solid-State Electronics</i> , 2005 , 49, 1009-1016	1.7	116
41	Crystalline silicon surface passivation with amorphous SiCx:H films deposited by plasma-enhanced chemical-vapor deposition. <i>Journal of Applied Physics</i> , 2005 , 98, 114912	2.5	21
40	Flexible Pentacene/PMMA Thin-Film Transistors Fabricated on Aluminium Foil Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 871, 1		2
39	Transverse Electrical Transport in Pentacene Photodiodes. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 871, 1		
38	Improvement of crystalline silicon surface passivation by hydrogen plasma treatment. <i>Applied Physics Letters</i> , 2004 , 84, 1474-1476	3.4	30
37	IR-study of a-SiCx:H and a-SiCxNy:H films for c-Si surface passivation. <i>Thin Solid Films</i> , 2004 , 451-452, 340-344	2.2	36
36	Pentacene thin-film transistors with polymeric gate dielectric. Organic Electronics, 2004, 5, 67-71	3.5	112
35	Electrical characterization of pentacene thin-film transistors with polymeric gate dielectric. <i>Synthetic Metals</i> , 2004 , 146, 355-358	3.6	19
34	Pentacene thin-film transistors on polymeric gate dielectric: device fabrication and electrical characterization. <i>Journal of Non-Crystalline Solids</i> , 2004 , 338-340, 617-621	3.9	36
33	Surface passivation of crystalline silicon by Cat-CVD amorphous and nanocrystalline thin silicon films. <i>Thin Solid Films</i> , 2003 , 430, 270-273	2.2	16
32	Pentacene thin-films obtained by thermal evaporation in high vacuum. <i>Thin Solid Films</i> , 2003 , 427, 367-3	37 <u>0</u> 2	45
31	Characterization and application of a-SiCx:H films for the passivation of the c-Si surface. <i>Thin Solid Films</i> , 2002 , 403-404, 476-479	2.2	9

30	Surface passivation of n-type crystalline Si by plasma-enhanced-chemical-vapor-deposited amorphous SiCx:H and amorphous SiCxNy:H films. <i>Applied Physics Letters</i> , 2002 , 81, 4461-4463	3.4	46
29	Characterization of a-SiCx:H Films for c-Si Surface Passivation. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 715, 2451		6
28	Electronic transport in low temperature nanocrystalline silicon thin-film transistors obtained by hot-wire CVD. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 400-404	3.9	8
27	Thin-film transistors with polymorphous silicon active layer. <i>Journal of Non-Crystalline Solids</i> , 2002 , 299-302, 1345-1350	3.9	10
26	Analysis of bias stress on thin-film transistors obtained by Hot-Wire Chemical Vapour Deposition. <i>Thin Solid Films</i> , 2001 , 383, 307-309	2.2	19
25	Stability of hydrogenated nanocrystalline silicon thin-film transistors. <i>Thin Solid Films</i> , 2001 , 395, 335-33	38 .2	26
24	Surface passivation of p-type crystalline Si by plasma enhanced chemical vapor deposited amorphous SiCx:H films. <i>Applied Physics Letters</i> , 2001 , 79, 2199-2201	3.4	115
23	Effects of thermal annealing in the properties of PECVD a-SiC layers. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 609, 2371		
22	Fabrication and characterization of in situ-doped a-Si0.8C0.2 emitter bipolar transistors. <i>Solid-State Electronics</i> , 2000 , 44, 1543-1548	1.7	5
21	Microcrystalline silicon thin film transistors obtained by hot-wire CVD. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000 , 69-70, 526-529	3.1	13
20	Thin film transistors obtained by hot wire CVD. Journal of Non-Crystalline Solids, 2000, 266-269, 1304-13	10,99	22
19	Large grid-connected hybrid PV system integrated in a public building. <i>Progress in Photovoltaics:</i> Research and Applications, 1998 , 6, 453-464	6.8	8
18	Infrared characterization of interfaces. <i>Applied Surface Science</i> , 1997 , 108, 211-217	6.7	
17	Study of post-deposition contamination in low-temperature deposited polysilicon films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1996 , 36, 96-99	3.1	3
16	Study of post-deposition contamination in low-temperature deposited polysilicon films 1996 , 96-99		
15	P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition. <i>Applied Surface Science</i> , 1995 , 86, 600-603	6.7	13
14	Deposition of Polysilicon Films by Hot-Wire CVD at Low Temperatures for Photovoltaic Applications. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 377, 63		8
13	Comparative study of trimethylboron doping of hot filament chemically vapour deposited and microwave plasma chemically vapour deposited diamond films. <i>Thin Solid Films</i> , 1994 , 253, 136-140	2.2	6

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12	Polycrystalline silicon films obtained by hot-wire chemical vapour deposition. <i>Applied Physics A:</i> Solids and Surfaces, 1994 , 59, 645-651		81
11	Trimethylboron doping of CVD diamond thin films. <i>Diamond and Related Materials</i> , 1994 , 3, 628-631	3.5	41
10	Influence of Substrate Temperature on the Properties of A-Si:H P-Layers Obtained from Trimethylboron. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 336, 565		1
9	On the determination of the interface density of states in a?Si:H/a?Si1&CX:H multilayers. <i>Journal of Non-Crystalline Solids</i> , 1993 , 164-166, 861-864	3.9	1
8	Carrier Injection in a-Si:H P-I-N Devices: Hydrogen Redistribution and Defect Creation. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 297, 315		1
7	Fast Degradation with Pulsed Light of a-Si:H P-I-N Photodiodes. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 297, 613		
6	Parallel Conduction in a-Si:H/a-Si1-xCx:H Multilayers. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 297, 699		
5	Structural characterization of a-SiC:H by thermal desorption spectroscopy. <i>Applied Surface Science</i> , 1993 , 70-71, 768-771	6.7	4
4	Structure of a-Si: H/a-Si1⊠Cx: H multilayers deposited in a reactor with automated substrate holder. <i>Vacuum</i> , 1993 , 44, 129-134	3.7	8
3	Persistent photoconductivity in undoped a-Si:H/a-SiC:H multilayers. <i>Thin Solid Films</i> , 1993 , 228, 165-168	2.2	
2	Optical and electrical characteristics of LEDs based on a single organic layer		1
1	Organic electronic devices: overview and future trends		1